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(12) **United States Design Patent**  
**Hori et al.**

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(54) **SEMICONDUCTOR DEVICE**

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(52) **U.S. Cl.**  
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(58) **Field of Classification Search**  
USPC ..... D13/110, 182; D7/509, 608, 619.1, D7/624.1, 624.2; 257/668, 678, 690; 361/713, 361/728, 736, 752, 775; 324/754, 755, 765  
See application file for complete search history.

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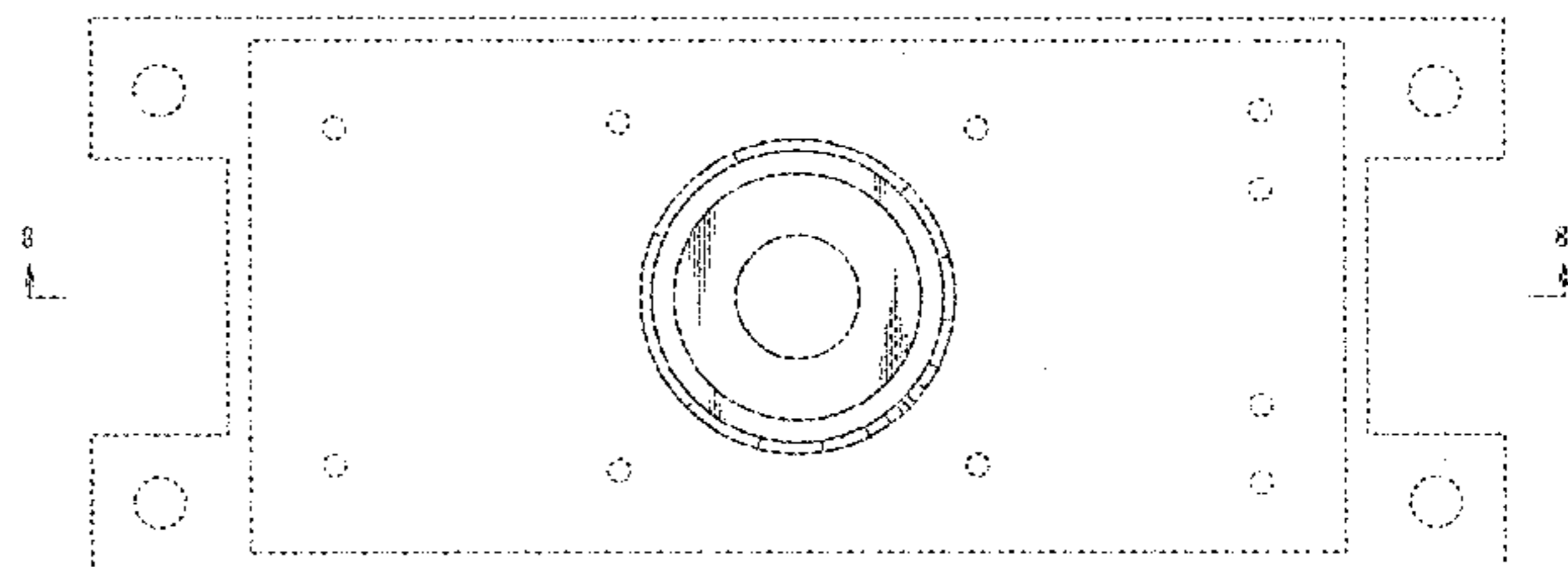
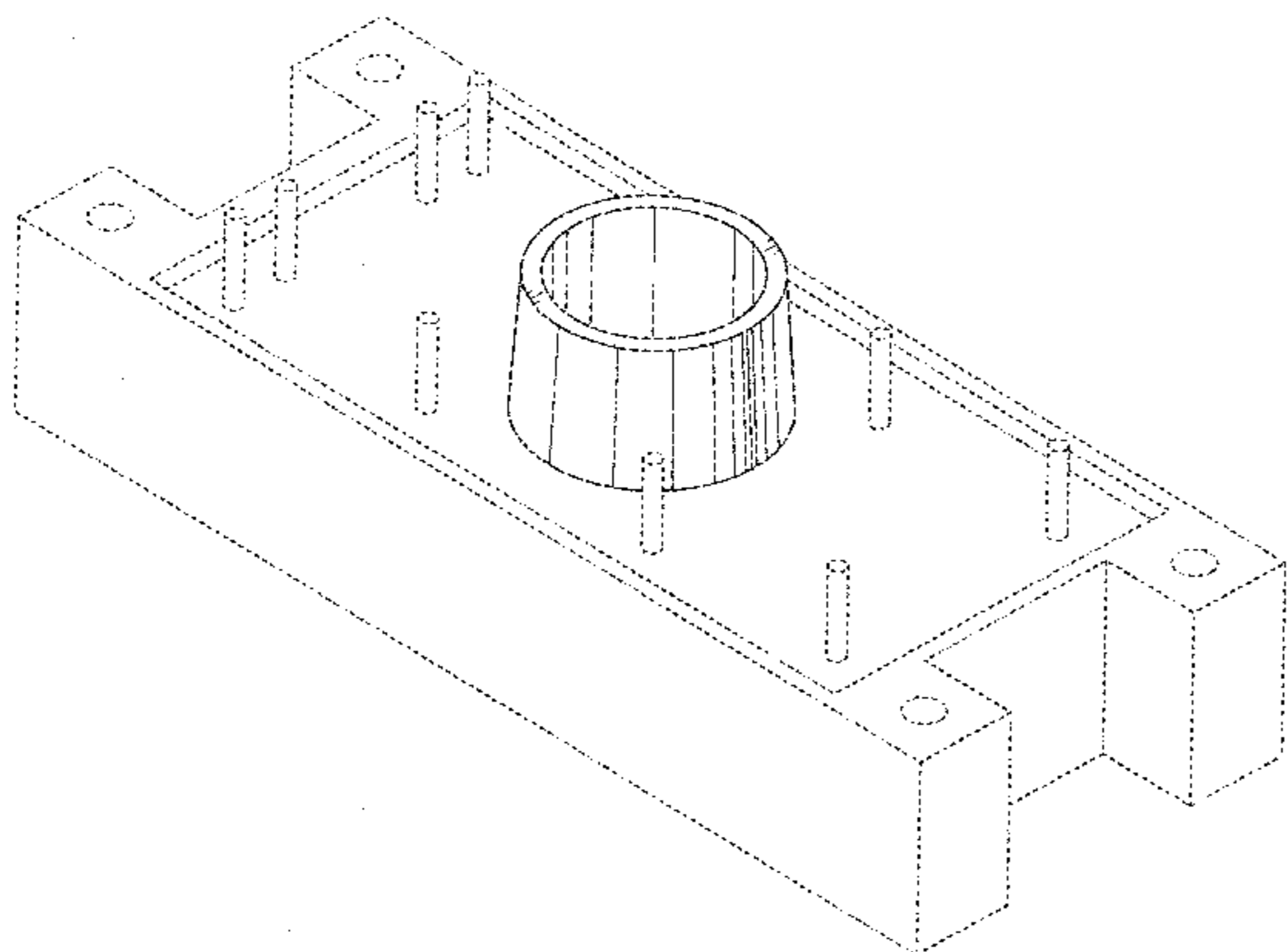
(57) **CLAIM**

The ornamental design for a semiconductor device, as shown and described.

**DESCRIPTION**

FIG. 1 is a front, top, right side perspective view of a semiconductor device showing our new design; FIG. 2 is a front view thereof; FIG. 3 is a rear view thereof; FIG. 4 is a top plan view thereof; FIG. 5 is a bottom plan view thereof; FIG. 6 is a left side view thereof; FIG. 7 is a right side view thereof; and, FIG. 8 is a cross sectional view taken along line 8-8 of FIG. 4. The broken lines shown in the drawings represent portions of the semiconductor device that form no part of the claimed design.

**1 Claim, 6 Drawing Sheets**



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Fig. 1

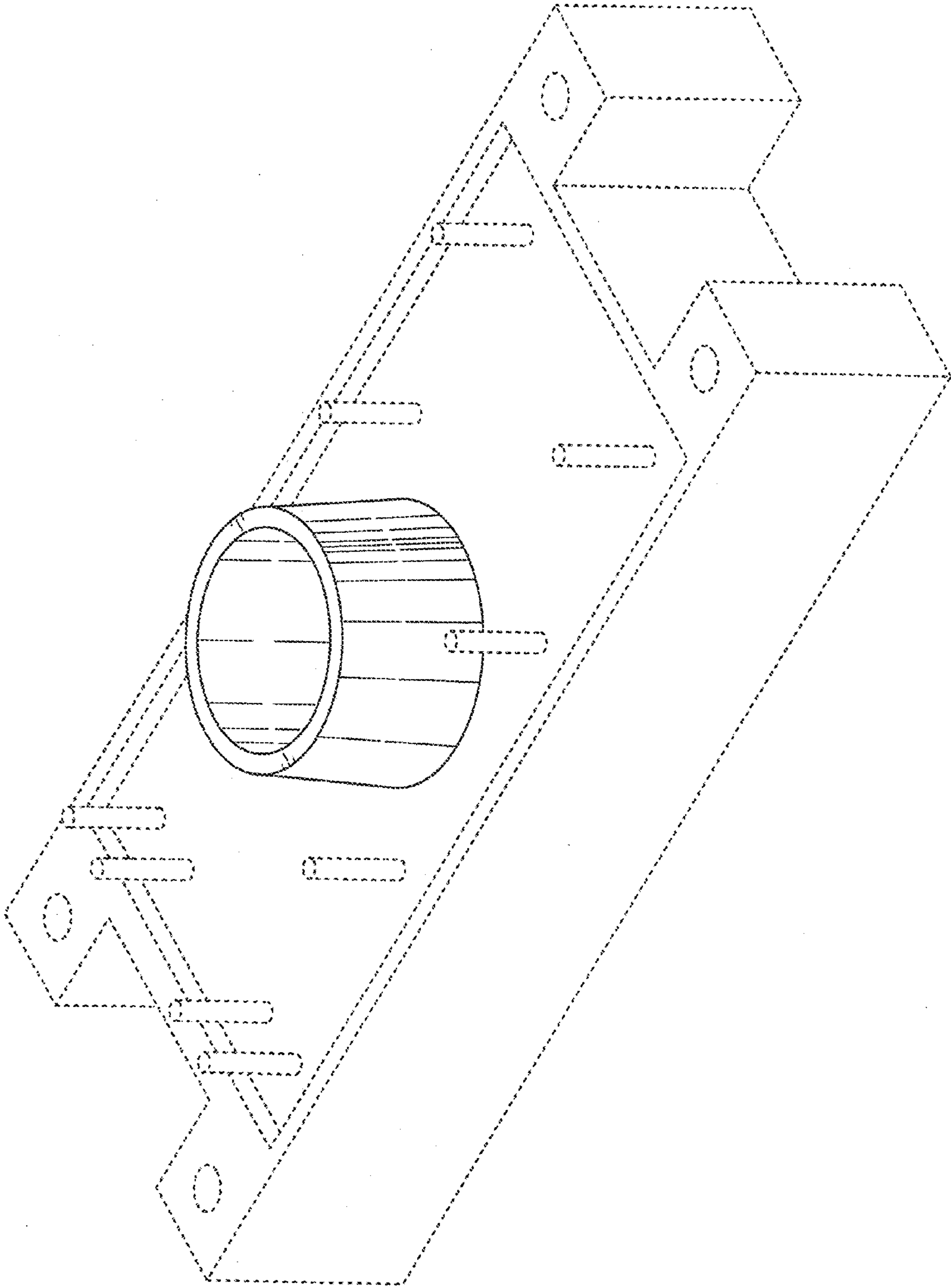


Fig. 2

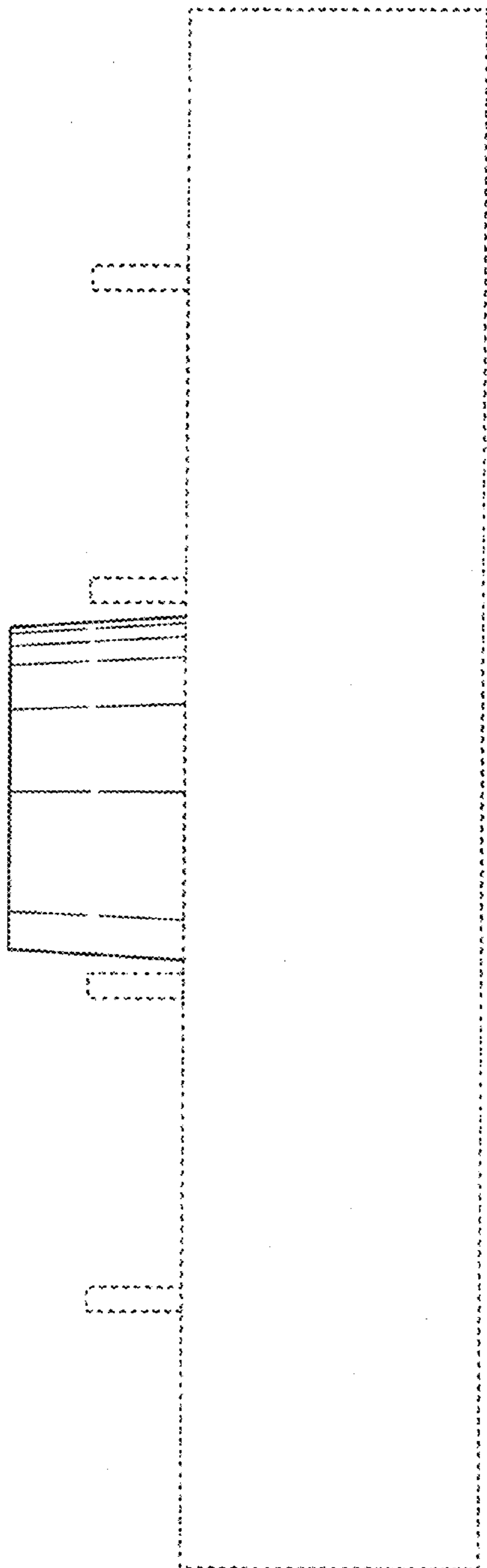


Fig. 3

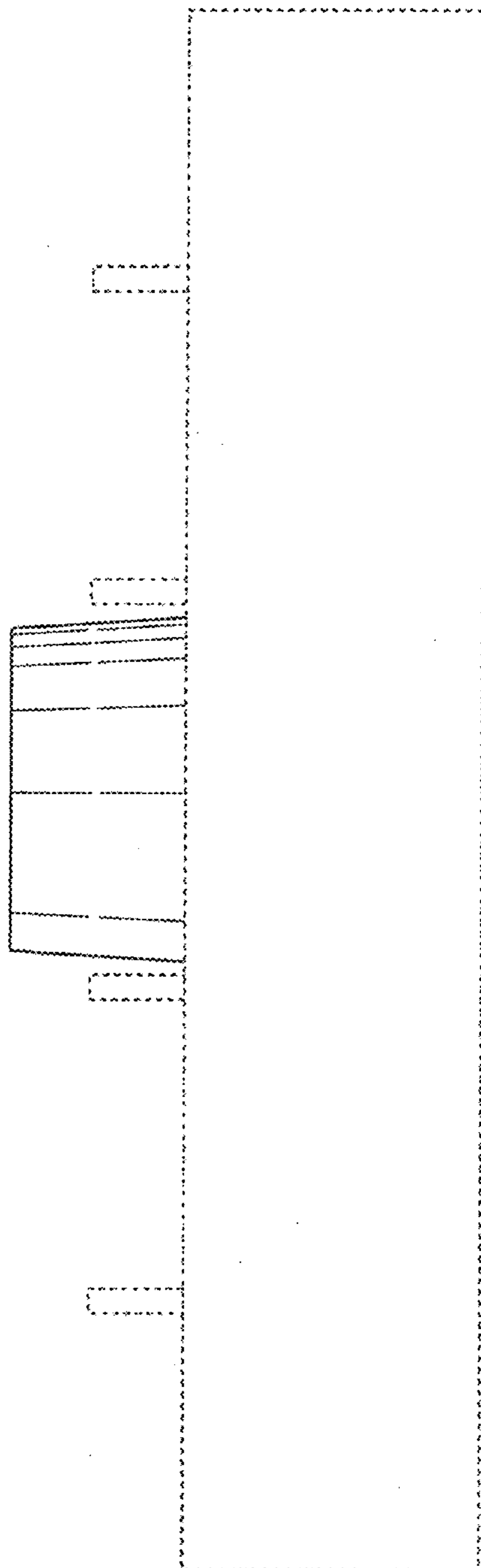


Fig. 4

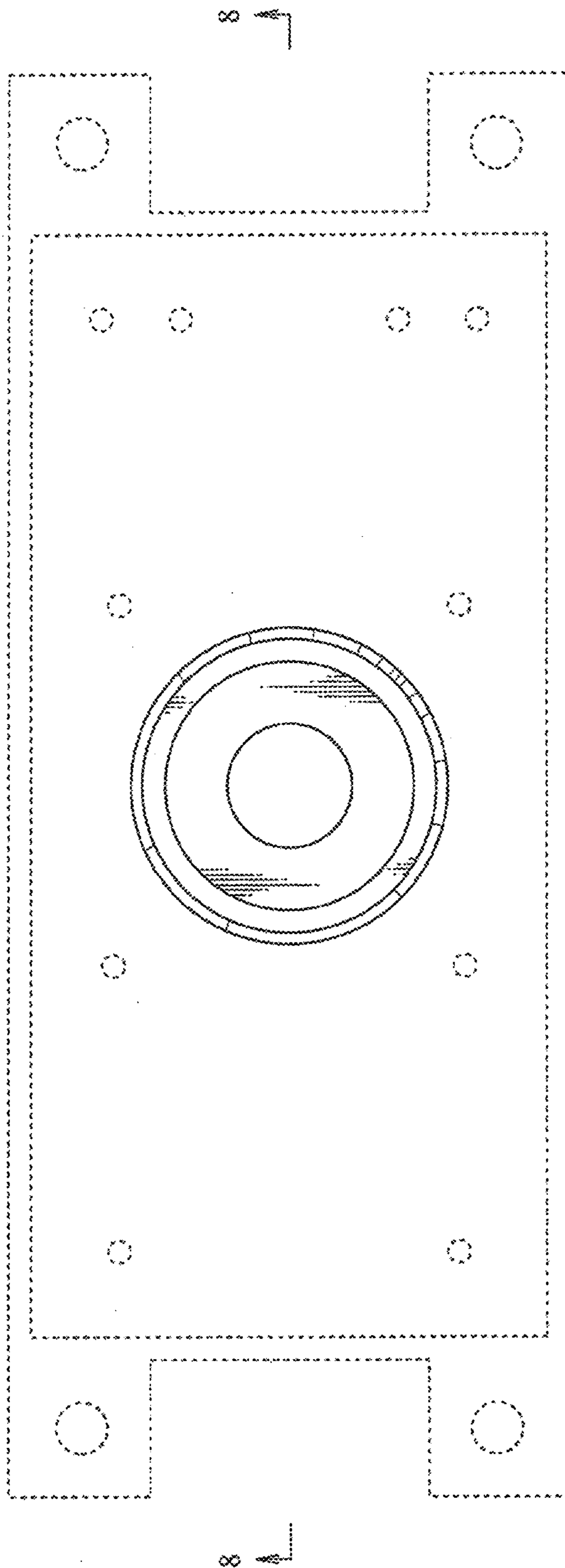


Fig. 5

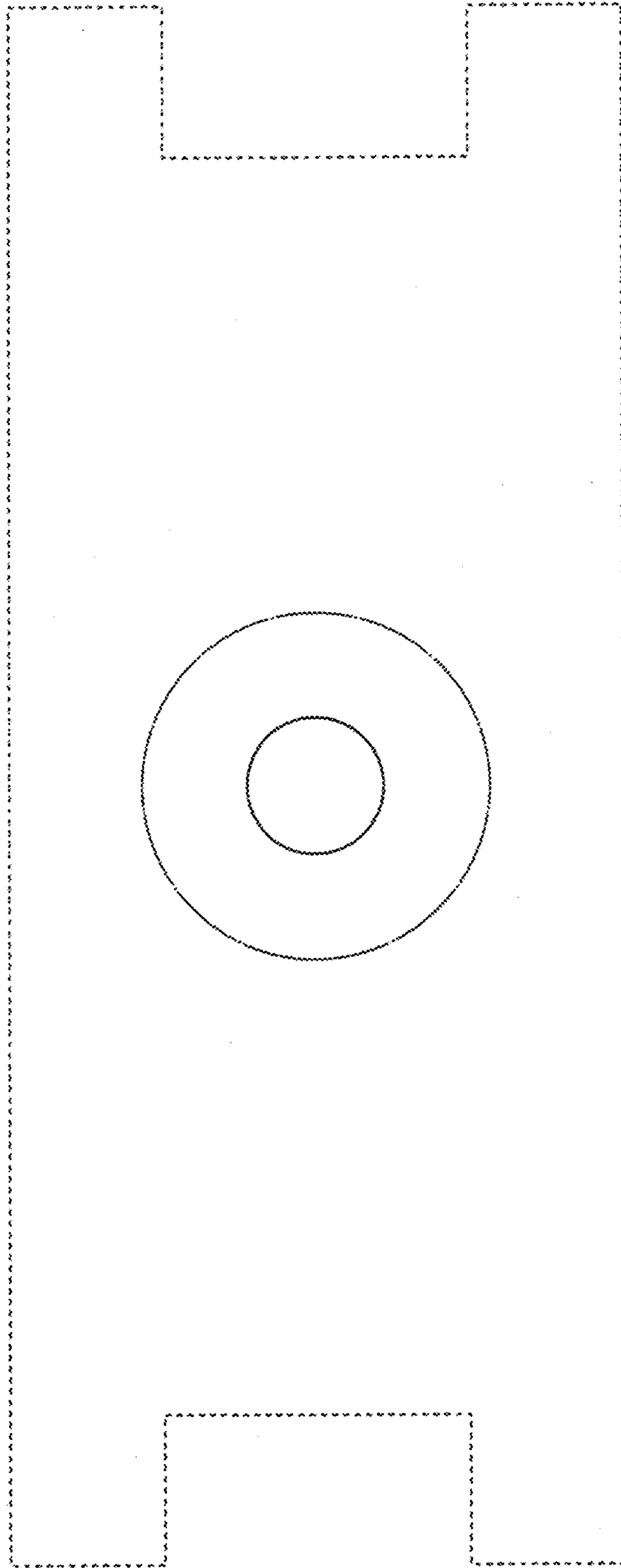


Fig. 7

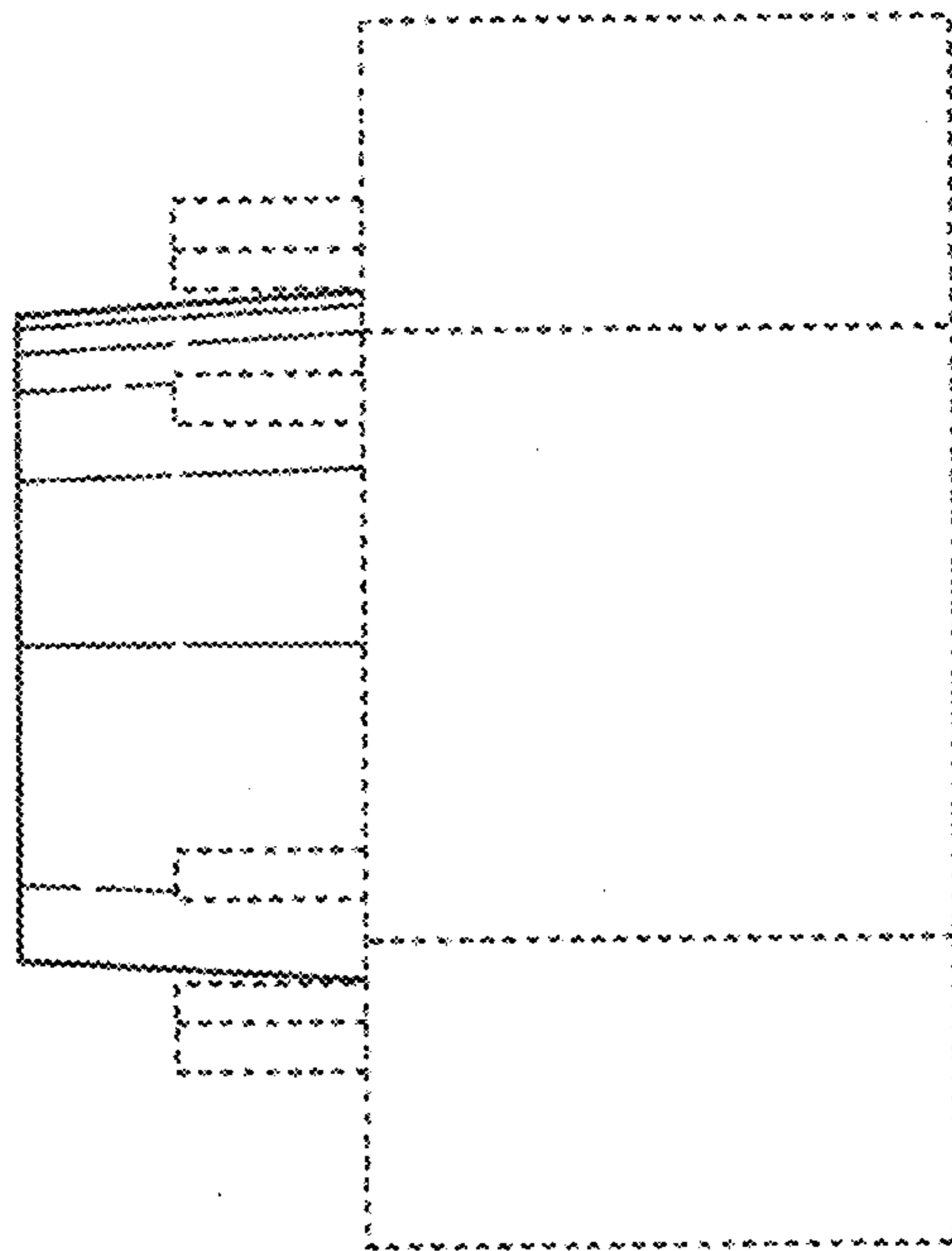


Fig. 6

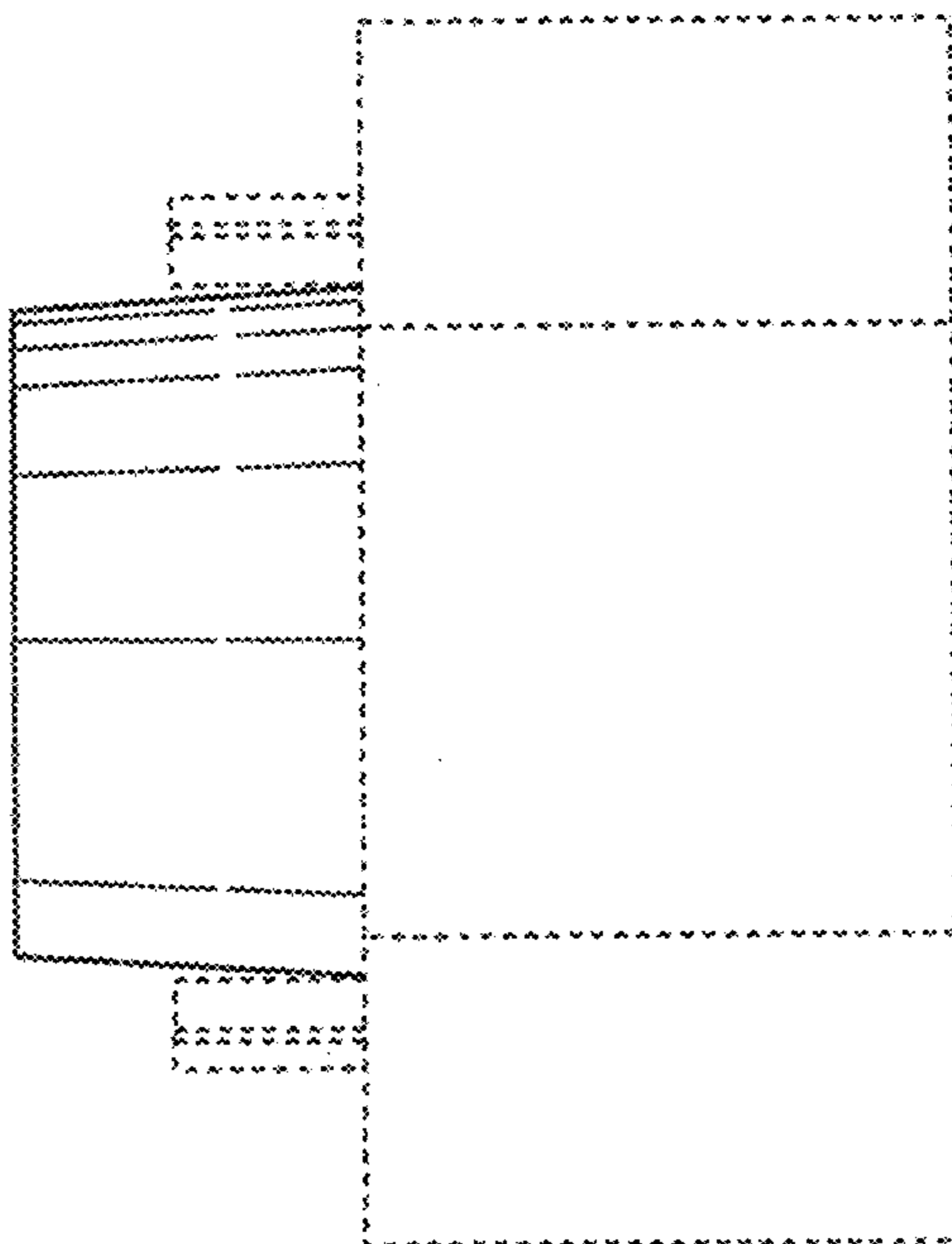


Fig. 8

